GEMaC
Groupe d'Étude
de la Matière Condensée

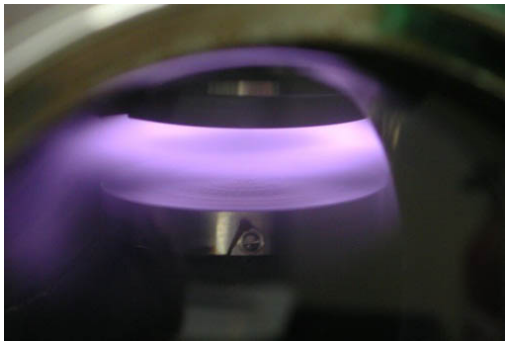
PRE- AND POST-GROWTH PROCESSING

High temperature annealing furnace

Model: Elite Thermal Systems TSH16/50/180
Annealing up to 1 600 °C under nitrogen flow, dedicated to semiconducting diamond.

Hydrogenation / Deuteration by capacitive plasma RF 13.56 MHz

For III-V, II-VI semiconductors
Model: reactor MECA2000
Conditions: 1 Torr, 25 - 500°C
Either sample in the plasma, or downstream (remote)



Hydrogenation / Deuteration by microwave plasma 1.45 GHz

For diamond
Model: Materia reactor used for diamond growth
Conditions: 10-20 Torr, 450 - 1 000 °C